

AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A semiconductor device, comprising:  
an insulating layer;  
an interconnect line embedded in said insulating layer;  
a circuit element mounted on said insulating layer;  
a packaging layer formed to cover said circuit element; and  
an electroconductive shielding film formed to cover said packaging layer,  
wherein:  
said interconnect line is electrically coupled to said shielding film;  
said shielding film is in contact with said packaging layer; and  
said shielding film and said packaging layer are formed of materials having a similar  
coefficient of linear expansion.
  
2. (Original) The semiconductor device according to claim 1, further comprising a  
protective film formed to cover said shielding film, said protective film comprising a material  
having higher corrosion resistance than that of a material that is included in said shielding film.
  
- Claims 3-9 (Canceled)
  
10. (New) The semiconductor device according to claim 1, wherein the interconnect  
line and the shielding film are formed of the same electro conductive material.